Low-Voltage CMOS Octal Transparent Latch Flow Through Pinout

With 5 V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The MC74LCX573 is a high performance, non–inverting octal transparent latch operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A $V_{\rm I}$ specification of 5.5 V allows MC74LCX573 inputs to be safely driven from 5.0 V devices.

The MC74LCX573 contains 8 D–type latches with 3–state standard outputs. When the Latch Enable (LE) input is HIGH, data on the Dn inputs enters the latches. In this condition, the latches are transparent, i.e., a latch output will change state each time its D input changes. When LE is LOW, the latches store the information that was present on the D inputs a setup time preceding the HIGH–to–LOW transition of LE. The 3–state standard outputs are controlled by the Output Enable ($\overline{\rm OE}$) input. When $\overline{\rm OE}$ is LOW, the standard outputs are enabled. When $\overline{\rm OE}$ is HIGH, the standard outputs are in the high impedance state, but this does not interfere with new data entering into the latches. The LCX573 flow through design facilitates easy PC board layout.

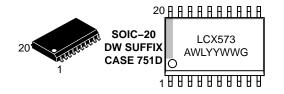
Features

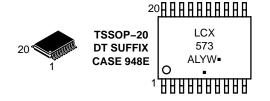
- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5.0 V Tolerant Interface Capability With 5.0 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0 \text{ V}$
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA)
 Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V Machine Model >200 V
- Pb-Free Packages are Available*

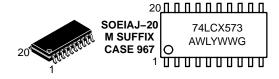


http://onsemi.com

MARKING DIAGRAMS







A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G = Pb-Free Package ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

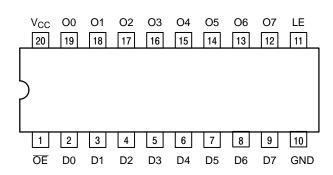


Figure 1. Pinout (Top View)

PIN NAMES

FUNCTION
Output Enable Input
Latch Enable Input
Data Inputs
3–State Latch Outputs

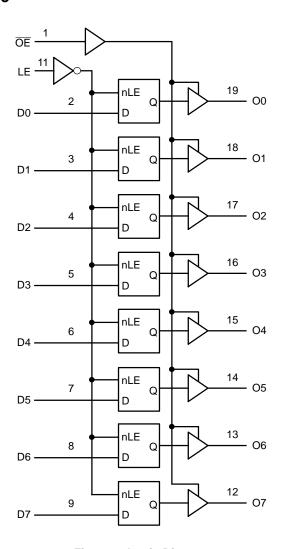


Figure 2. Logic Diagram

TRUTH TABLE

	INPUTS		OUTPUTS	
OE	LE	Dn	On	OPERATING MODE
L L	H H	H	H L	Transparent (Latch Disabled); Read Latch
L L	L L	h I	H L	Latched (Latch Enabled) Read Latch
L	L	Х	NC	Hold; Read Latch
Н	L	Х	Z	Hold; Disabled Outputs
H	H H	H L	Z Z	Transparent (Latch Disabled); Disabled Outputs
H H	L L	h I	Z Z	Latched (Latch Enabled); Disabled Outputs

H = High Voltage Level;

h = High Voltage Level One Setup Time Prior to the Latch Enable High-to-Low Transition

L = Low Voltage Level

I = Low Voltage Level One Setup Time Prior to the Latch Enable High-to-Low Transition

NC = No Change, State Prior to the Latch Enable High-to-Low Transition

X = High or Low Voltage Level or Transitions are Acceptable

Z = High Impedance State

For I_{CC} Reasons DO NOT FLOAT Inputs

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
V _L	DC Input Voltage	$-0.5 \le V_{I} \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_{O} \le +7.0$	Output in 3-State	V
		$-0.5 \le V_{O} \le V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1)	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
Io	DC Output Source/Sink Current	±50		mA
Icc	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Paran	neter	Min	Тур	Max	Unit
V _{CC}	Supply Voltage	Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	3.6 3.6	V
VI	Input Voltage		0		5.5	V
V _O	Output Voltage	(HIGH or LOW State) (3–State)	0 0		V _{CC} 5.5	V
I _{OH}	HIGH Level Output Current	$V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$ $V_{CC} = 2.3 \text{ V} - 2.7 \text{ V}$			- 24 - 12 - 8	mA
I _{OL}	LOW Level Output Current	$V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$ $V_{CC} = 2.3 \text{ V} - 2.7 \text{ V}$			+ 24 + 12 + 8	mA
T _A	Operating Free-Air Temperature		-40		+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, VIN	from 0.8 V to 2.0 V, V _{CC} = 3.0 V	0		10	ns/V

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LCX573DW	SOIC-20	38 Units / Rail
MC74LCX573DWG	SOIC-20 (Pb-Free)	38 Units / Rail
MC74LCX573DWR2	SOIC-20	1000 Tape & Reel
MC74LCX573DWR2G	SOIC-20 (Pb-Free)	1000 Tape & Reel
MC74LCX573DT	TSSOP-20*	75 Units / Rail
MC74LCX573DTG	TSSOP-20*	75 Units / Rail
MC74LCX573DTR2	TSSOP-20*	2000 Tape & Reel
MC74LCX573DTR2G	TSSOP-20*	2000 Tape & Reel
MC74LCX573M	SOEIAJ-20	40 Units / Rail
MC74LCX573MG	SOEIAJ-20 (Pb-Free)	40 Units / Rail
MC74LCX573MEL	SOEIAJ-20	2000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{1.} I_O absolute maximum rating must be observed.

^{*}This package is inherently Pb-Free.

DC ELECTRICAL CHARACTERISTICS

			T _A = -40°C	to +85°C	
Symbol	Characteristic	Condition	Min	Max	Unit
V _{IH}	HIGH Level Input Voltage (Note 2)	2.3 V ≤ V _{CC} ≤ 2.7 V	1.7		V
		2.7 V ≤ V _{CC} ≤ 3.6 V	2.0		1
V _{IL}	LOW Level Input Voltage (Note 2)	2.3 V ≤ V _{CC} ≤ 2.7 V		0.7	V
		2.7 V ≤ V _{CC} ≤ 3.6 V		0.8	1
V _{OH}	HIGH Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$	V _{CC} - 0.2		V
		$V_{CC} = 2.3 \text{ V; } I_{OH} = -8 \text{ mA}$	1.8		1
		$V_{CC} = 2.7 \text{ V}; I_{OH} = -12 \text{ mA}$	2.2		1
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -18 \text{ mA}$	2.4		1
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -24 \text{ mA}$	2.2		1
V _{OL}	LOW Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$		0.2	V
		V _{CC} = 2.3 V; I _{OL} = 8 mA		0.6	1
		$V_{CC} = 2.7 \text{ V; } I_{OL} = 12 \text{ mA}$		0.4	1
		V _{CC} = 3.0 V; I _{OL} = 16 mA		0.4	1
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55	1
I _I	Input Leakage Current	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le \text{V}_{I} \le 5.5 \text{ V}$		±5	μΑ
I _{OZ}	3-State Output Current	$2.3 \le V_{CC} \le 3.6 \text{ V}; 0V \le V_{O} \le 5.5 \text{ V};$ $V_{I} = V_{IH} \text{ or } V_{IL}$		±5	μΑ
l _{OFF}	Power-Off Leakage Current	$V_{CC} = 0 \text{ V; } V_{I} \text{ or } V_{O} = 5.5 \text{ V}$		10	μΑ
I _{CC}	Quiescent Supply Current	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$		10	μΑ
		$2.3 \le V_{CC} \le 3.6 \text{ V}; 3.6 \le V_{I} \text{ or } V_{O} \le 5.5 \text{ V}$		±10	1
ΔI_{CC}	Increase in I _{CC} per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500	μΑ

^{2.} These values of V_I are used to test DC electrical characteristics only.

AC CHARACTERISTICS $t_R = t_F = 2.5 \text{ ns}; \ R_L = 500 \ \Omega$

				Limits					
					T _A = -40°0	C to +85°C			
			V _{CC} = 3.3	3 V ± 0.3 V	V _{CC} =	: 2.7 V	V _{CC} = 2.5	$V \pm 0.2 V$	
			C _L =	50 pF	C _L =	50 pF	C _L =	30 pF	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Unit
t _{PLH} t _{PHL}	Propagation Delay D _n to O _n	1	1.5 1.5	8.0 8.0	1.5 1.5	9.0 9.0	1.5 1.5	9.6 9.6	ns
t _{PLH} t _{PHL}	Propagation Delay LE to O _n	3	1.5 1.5	8.5 8.5	1.5 1.5	9.5 9.5	1.5 1.5	10.5 10.5	ns
t _{PZH}	Output Enable Time to HIGH and LOW Level	2	1.5 1.5	8.5 8.5	1.5 1.5	9.5 9.5	1.5 1.5	10.5 10.5	ns
t _{PHZ} t _{PLZ}	Output Disable Time From High and Low Level	2	1.5 1.5	6.5 6.5	1.5 1.5	7.0 7.0	1.5 1.5	7.8 7.8	ns
t _s	Setup Time, HIGH or LOW D _n to LE	3	2.5		2.5		4.0		
t _h	Hold Time, HIGH or LOW D_n to LE	3	1.5		1.5		2.0		
t _w	LE Pulse Width, HIGH	3	3.3		3.3		4.0		
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 3)			1.0 1.0					ns

^{3.} Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

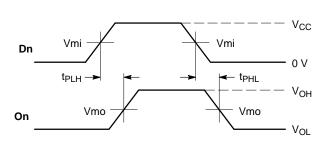
DYNAMIC SWITCHING CHARACTERISTICS

			Т	A = +25°C	;	
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OLP}	Dynamic LOW Peak Voltage (Note 4)	$\begin{aligned} & V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ & V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{aligned}$		0.8 0.6		V V
V _{OLV}	Dynamic LOW Valley Voltage (Note 4)	$\begin{aligned} & V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ & V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{aligned}$		-0.8 -0.6		V V

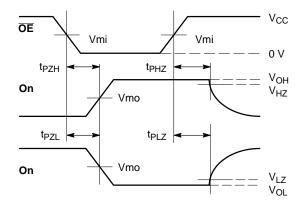
^{4.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

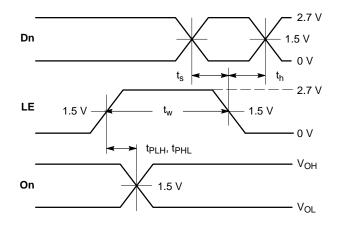
Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	7	pF
C _{I/O}	Input/Output Capacitance	$V_{CC} = 3.3 \text{ V}, V_{I} = 0 \text{ V or } V_{CC}$	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	25	pF



WAVEFORM 1 – PROPAGATION DELAYS $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$



WAVEFORM 2 – OUTPUT ENABLE AND DISABLE TIMES $t_R = t_F = 2.5 \text{ ns}$, 10% to 90%; f = 1 MHz; $t_W = 500 \text{ ns}$

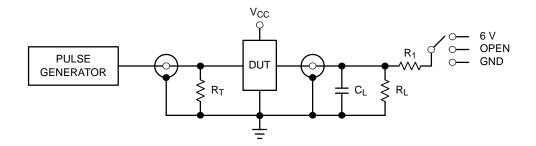


	Vcc				
Symbol	3.3 V ± 0.3 V	2.7 V	2.5 V ± 0.2 V		
Vmi	1.5 V	1.5 V	V _{CC} /2		
Vmo	1.5 V	1.5 V	V _{CC} /2		
V _{HZ}	V _{OL} + 0.3 V	V _{OL} + 0.3 V	V _{OL} + 0.15 V		
V _{LZ}	V _{OL} – 0.3 V	V _{OL} – 0.3 V	V _{OL} – 0.15 V		

WAVEFORM 3 – LE to On PROPAGATION DELAYS, LE MINIMUM PULSE WIDTH, Dn to LE SETUP AND HOLD TIMES

 $t_R = t_F = 2.5$ ns, 10% to 90%; f = 1 MHz; $t_W = 500$ ns except when noted

Figure 3. AC Waveforms



TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	6 V at V_{CC} = 3.3 \pm 0.3 V 6 V at V_{CC} = 2.5 \pm 0.2 V
Open Collector/Drain t _{PLH} and t _{PHL}	6 V
t _{PZH} , t _{PHZ}	GND

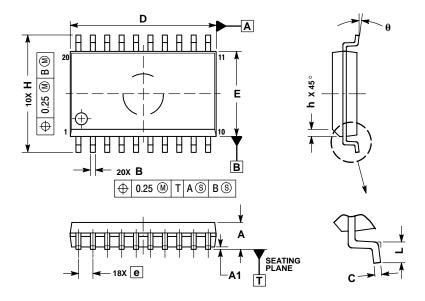
 C_L = 50 pF at V_{CC} = 3.3 \pm 0.3 V or equivalent (includes jig and probe capacitance) C_L = 30 pF at V_{CC} = 2.5 \pm 0.2 V or equivalent (includes jig and probe capacitance) R_L = R_1 = 500 Ω or equivalent

 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

PACKAGE DIMENSIONS

SOIC-20 **DW SUFFIX** CASE 751D-05 ISSUE G



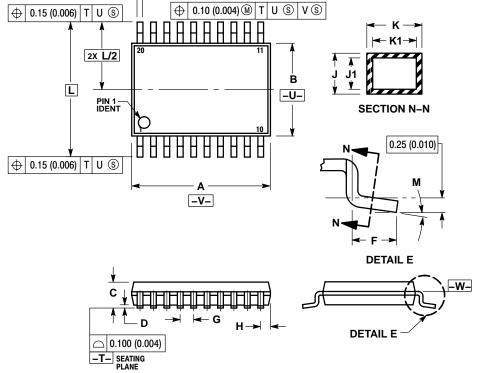
20X **K** REF

NOTES:

- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES
 PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
- PROTRUSION: MAXIMUM MOLD PROTRUSION 0.15 PER SIDE. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
θ	0 °	7 °		

TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE B**



NOTES:

- DTES:

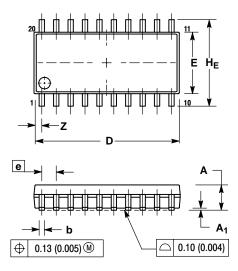
 1. DIMENSIONING AND TOLERANCING
 PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION:
 MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE
 MOLD FLASH, PROTRUSIONS OR GATE
 BURRS. MOLD FLASH OR GATE BURRS
 SHALL NOT EXCEED 0.15 (0.006) PER
 SIDE SIDE.
 4. DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION.
 SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE
- DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08 DAMBAR FOR THOSING STALL BOOM (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 3. TERMINAL NUMBERS ARE SHOWN
- FOR REFERENCE ONLY.

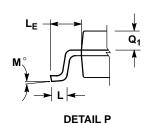
 7. DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

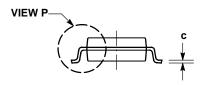
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

PACKAGE DIMENSIONS

SOEIAJ-20 **M SUFFIX** CASE 967-01 **ISSUE O**







NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS D AND E DO NOT INCLIDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE
 BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LΕ	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
Q1	0.70	0.90	0.028	0.035
Z		0.81		0.032

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